YJ Planar Schottky Barrier Diode Die Specification

60V 2A, 40mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB040M060SS-280A

Main Products Characterstics

Maximum Ratings

		Rating
Repetitive peak reverse voltage	V_{RRM}	60 V
Average forward current		

Static Electrical Characteristics (Ta = 25°C)

Parameter		Symbol
Reverse breakdown voltage I_R = 1mA = 2	≤ 2%	V_{BR}
Maximum reverse current $V_R = V_{RRM}$	≤ 2%	I_R

Device Schematics and Outline Drawing

Die Thickness *	
Die Size **	40 Mils
Top Metal Pad	
Active Area	
Top Metal	
Back Metal	Ag

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

0514-80982389
0514-80980189

Rev.O 2021/07/28